

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously presented) A semiconductor device comprising:
a gate interconnection and a source interconnection formed over a substrate; and
an insulating film formed between the gate interconnection and the source interconnection in
a region where the gate interconnection and the source interconnection intersect.

2. (Previously presented) A semiconductor device comprising:
a gate interconnection and a source interconnection formed over a substrate, and
an island-like insulating film formed between the gate interconnection and the source
interconnection in a region where the gate interconnection and the source interconnection intersect.

3. (Previously presented) A semiconductor device comprising:
a gate interconnection and a source interconnection formed over a substrate; and
an island-like insulating film formed between the gate interconnection and the source
interconnection in a region where the gate interconnection and the source interconnection intersect;
wherein the gate interconnection and the source interconnection are formed on a same
insulating surface in a region where the gate interconnection and the source interconnection do not
intersect.

4. (Previously presented) A semiconductor device according to any one of claims 2 and 3,
wherein the island-like insulating layer is formed so as to cover the gate interconnection in a

region where the gate interconnection and the source interconnection intersect; and
wherein the source interconnection is formed over the island-like insulating layer.

5. (Previously presented) A semiconductor device according to any one of claims 2 and 3,
wherein the island-like insulating layer is formed so as to cover the source interconnection in
a region where the gate interconnection and the source interconnection intersect; and
wherein the gate interconnection is formed over the island-like insulating layer.

6. (Previously presented) A semiconductor device comprising:

a source region and a source interconnection formed over a substrate; and

the source region and the source interconnection connected on a same plane.

7. (Previously presented) A semiconductor device according to claim 6
wherein the source region and the source interconnection are connected without through a
contact hole.

8. (Previously presented) A semiconductor device according to any one of claims 1 to 3
wherein at least one of the gate interconnection and the source interconnection is formed by
discharging a solution containing metal particles.

9. (Previously presented) A semiconductor device according to any one of claims 1 to 3

wherein at least one of the gate interconnection and the source interconnection is formed by discharging a solution containing metal elements.

10. (Previously presented) A semiconductor device according to claim 1 wherein the insulating film is formed by discharging a solution containing an insulating material.

11. (Previously presented) A semiconductor device according to any one of claims 2 and 3 wherein the island-like insulating layer is formed by discharging a solution containing an insulating material.

12. (Previously presented) A semiconductor device according to any one of claims 1 to 3 and 5 wherein the semiconductor device includes a thin film transistor using a microcrystalline semiconductor.

13. (Previously presented) A semiconductor device according to any one of claims 1 to 3 and 5 wherein the semiconductor device includes a thin film transistor using an organic semiconductor.

14-20 (Canceled)

21. (Original) A display device including the semiconductor device according to any one of claims 1 to 3 and 5.

22. (Original) A digital still camera including the semiconductor device according to any one of claims 1 to 3 and 5.

23. (Original) A personal computer including the semiconductor device according to any one of claims 1 to 3 and 5.

24. (Original) A mobile computer including the semiconductor device according to any one of claims 1 to 3 and 5.

25. (Original) An image reproducing system including the semiconductor device according to any one of claims 1 to 3 and 5.